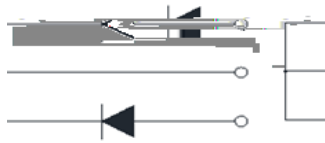
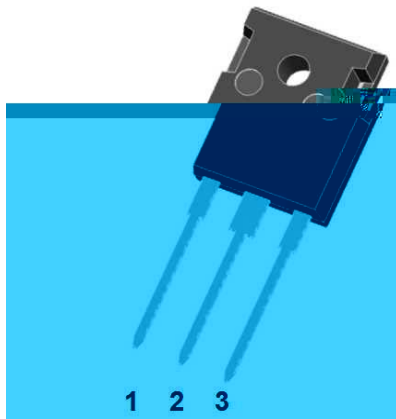


Schottky Diodes



Features

- < igh fre e uency operation
- Low forward voltage drop
- < igh purity ž high temperature epoxy encapsulation for enhanced mechanical strength
- 7 H U P L C T D plated leads ž solderable
- 002 and > ESD22-B102
- Polarity: As marked

Maximum Ratings (Ta 1 2) Unless otherwise specified

PARAMETER	SYMBOL	UNIT	MBR20200PT
Device marking code			MBR20200PT
Repetitive Peak Reverse Voltage	VRRM	V	200
Average Rectified Output Current 4 60 < n sine wave ž R-load (1 7)	IO	A	20
Surge(Non-repetitive)Forward Current 4 60 < n half sine-wave ž 1 cycle ž Ta 1 2)	IFSM	A	200
Current Se uared Time 4 1ms@t@8.3ms T ^ 1 2)	I²t	A²s	166
Storage Temperature	Tstg		-)) r Ž 17)
> unction Temperature	T ^		-)) r Ž 17)

Electrical Characteristics

PARAMETER	SYMBOL	UNIT	TEST CONDITIONS	Min	Typ	Max
Peak Forw 1 10.0A T ^ 1 1 2)				0.68	0.72	
DC reverse current at rated DC blocking voltage per diode	I _{RRM1}			-	-	20
> unction capacitance	C ^		1M < N Applied Voltage V.D.C. and Reverse of 4.0	100	1) 8	300

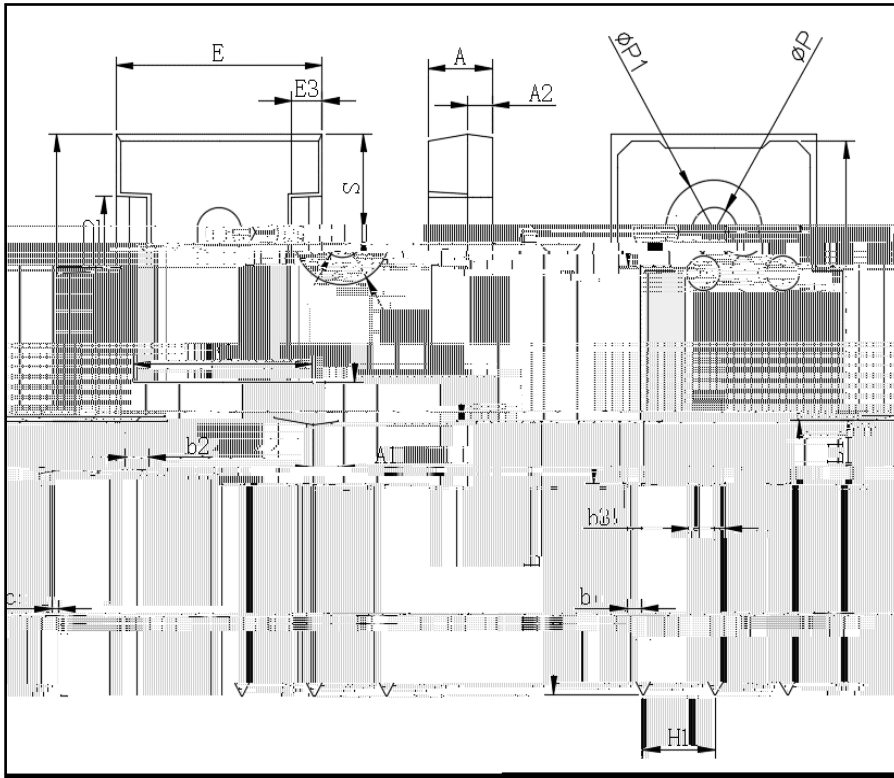
Note1:Pulse test:300uS pulse width ž 1% duty cycle

Note2:Pulse test:pulse width 40mS



MBR20200PT

Outline Dimensions



TO-247AB		
Dim	Min	Max
A	4.80) .20
A1	2.21	2.61
A2	1.8)	2.1)
b	1.0	1.4
b2	1. - 1	2.21
C	0.)	0.7
D	20.70	21.30
D1	16.2)	16.8)
E	1) .) 0	16.10
E1	13.0	13.6
E2	4.80) .20
E3	2.30	2.70
L	1 - .62	20.22
L1	-	4.30
P	3.40	3.80
P1	-	7.30
S	6.1) TYP	
<1) .44TYP	
b3	2.80	3.20

